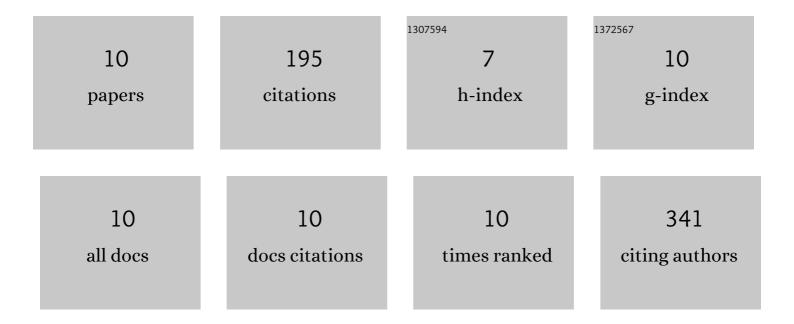
## Maria Androulidaki

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Nanofabrication of normally-off GaN vertical nanowire MESFETs. Nanotechnology, 2019, 30, 285304.	2.6	15
2	Improved GaN Quantum Well Microcavities for Robust Room Temperature Polaritonics. Physica Status Solidi (B): Basic Research, 2019, 256, 1800716.	1.5	5
3	Mathematical assessment of the thermal band gap variation of semiconductors. Physica Scripta, 2019, 94, 085701.	2.5	7
4	Optical properties of InGaN thin films in the entire composition range. Journal of Applied Physics, 2018, 123, .	2.5	37
5	The thermo-electric nature of the Debye temperature. AIP Advances, 2018, 8, 055318.	1.3	2
6	Selective-area growth of GaN nanowires on SiO2-masked Si (111) substrates by molecular beam epitaxy. Journal of Applied Physics, 2016, 119, 224305.	2.5	29
7	Effect of rapid thermal annealing on polycrystalline InGaN thin films deposited on fused silica substrates. Thin Solid Films, 2016, 611, 46-51.	1.8	10
8	Understanding the effects of Si (111) nitridation on the spontaneous growth and properties of GaN nanowires. Journal of Crystal Growth, 2016, 442, 8-13.	1.5	19
9	Molecular beam epitaxy of thick InGaN(0001) films: Effects of substrate temperature on structural and electronic properties. Journal of Crystal Growth, 2016, 437, 20-25.	1.5	25
10	InGaN(0001) alloys grown in the entire composition range by plasma assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 102-105.	1.8	46